

TMG60P06NF

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = -60V$ $I_D = -60A$

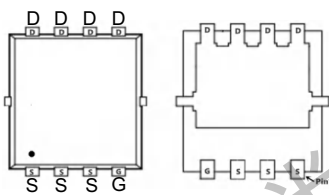
$R_{DS(ON)} = 12m\Omega (typ.) @ V_{GS} = -10V$

100% UIS Tested

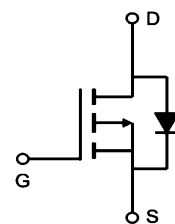
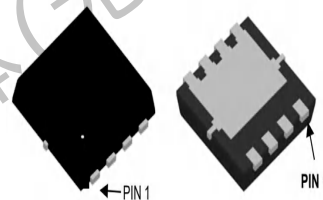
100% R_g Tested



NF:DFN5x6-8L



Marking: G60P06



Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V$	-60	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V$	-38	A
I_{DM}	Pulsed Drain Current	-240	A
EAS	Single Pulse Avalanche Energy	337	mJ
P_D	Total Power Dissipation	114	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	3.6	$^\circ C/W$

TMG60P06NF

P-Channel Enhancement Mosfet

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified) :

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS} = -60V, V_{GS}= 0V$	--	--	1	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS} = -20V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS} = +20V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-2.0	-3.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-20A$	--	12	16	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=-4.5V, I_D=-10A$	--	16	20	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$ $V_{DS}=-30V$ $f=1.0MHz$	--	2630	--	pF
C_{oss}	Output Capacitance		--	484	--	
C_{rss}	Reverse Transfer Capacitance		--	9.4	--	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}$ Open	--	12.5	--	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=-10A, R_L=3.0\Omega$ $V_{DS}= -30V$ $V_{GS}= -10V$ $R_G= 3\Omega$	--	20	--	ns
t_r	Rise Time		--	25	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	60	--	
t_f	Fall Time		--	30	--	
Q_g	Total Gate Charge	$V_{GS}=-10V$ $V_{DS}=-30V$ $I_D=-10A$	--	38	--	nC
Q_{gs}	Gate Source Charge		--	6.9	--	
Q_{gd}	Gate Drain Charge		--	4.98	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25^\circ\text{C}$	--	--	-60	A
V_{SD}	Diode Forward Voltage	$I_S=-5.0A, V_{GS}=0V$	--	--	-1.2	V
t_{rr}	Reverse Recovery time	$I_S=-10A, V_{DD}=-30V$ $dI/dt=100A/\mu s$	--	50	--	ns
Q_{rr}	Reverse Recovery Charge		--	80	--	nC

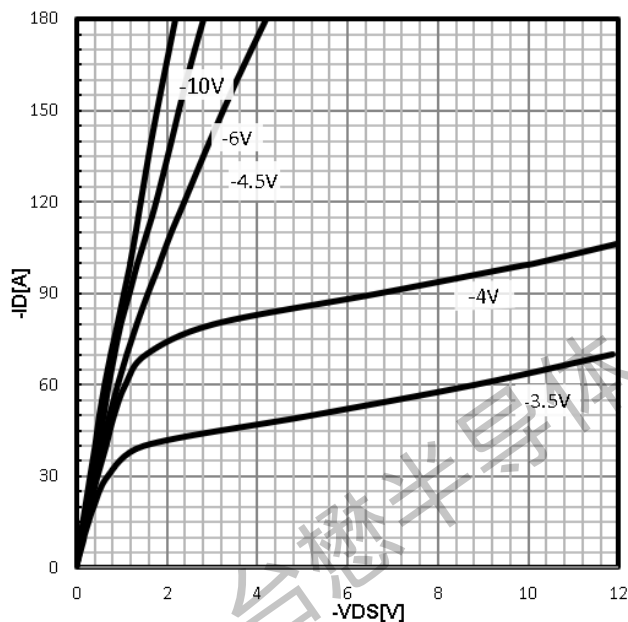
TMG60P06NF

P-Channel Enhancement Mosfet

Characteristics Curve:

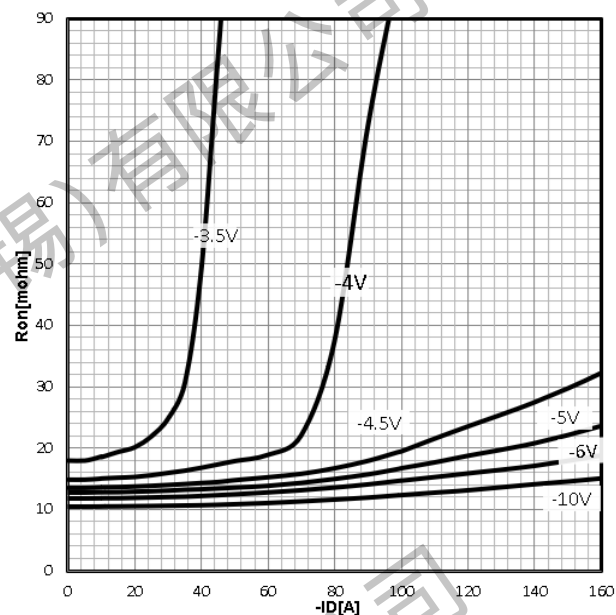
Typ. output characteristics

$$-I_D = f(-V_{DS})$$



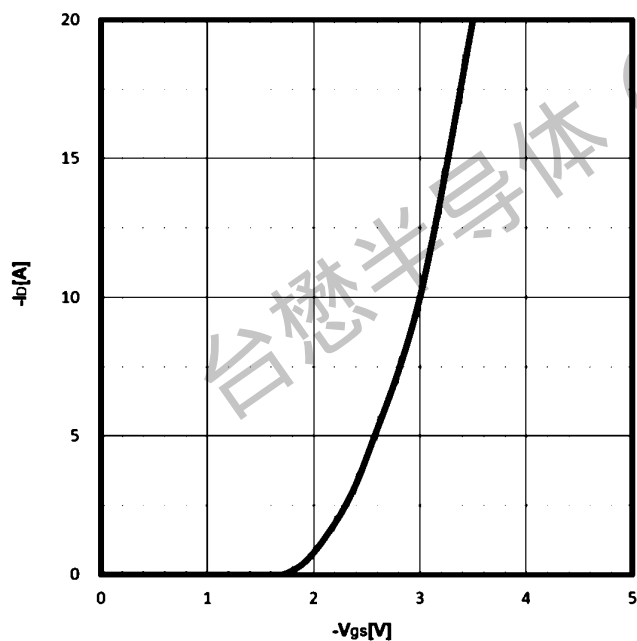
Typ. drain-source on resistance

$$R_{DS(on)} = f(-I_D)$$



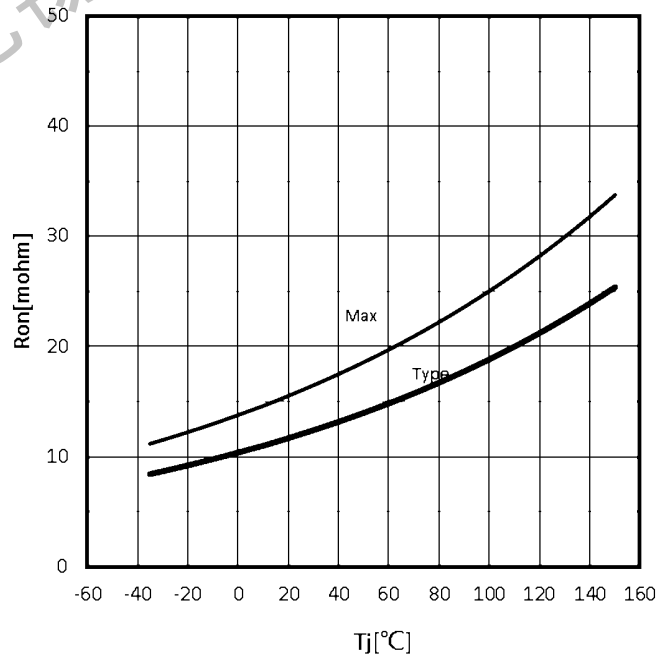
Typ. transfer characteristics

$$-I_D = f(-V_{GS})$$



Drain-source on-state resistance

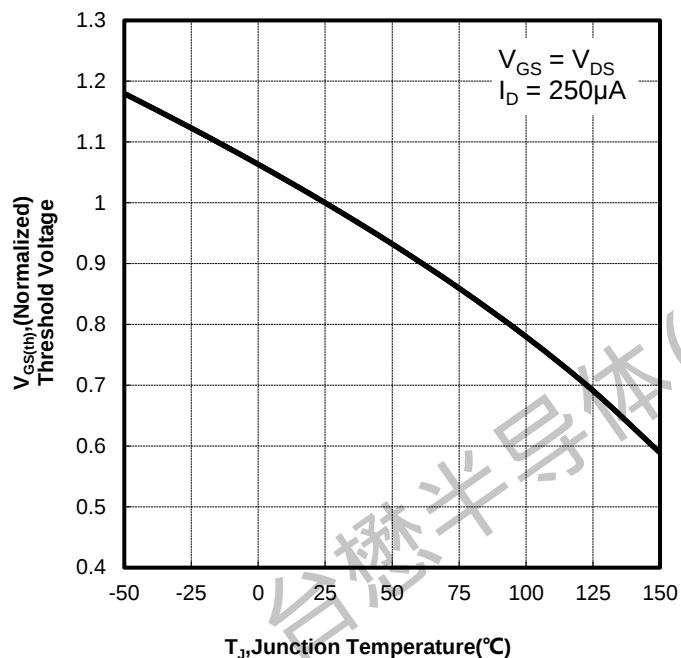
$$R_{DS(on)} = f(T_j); I_D = -20A; V_{GS} = -10V$$



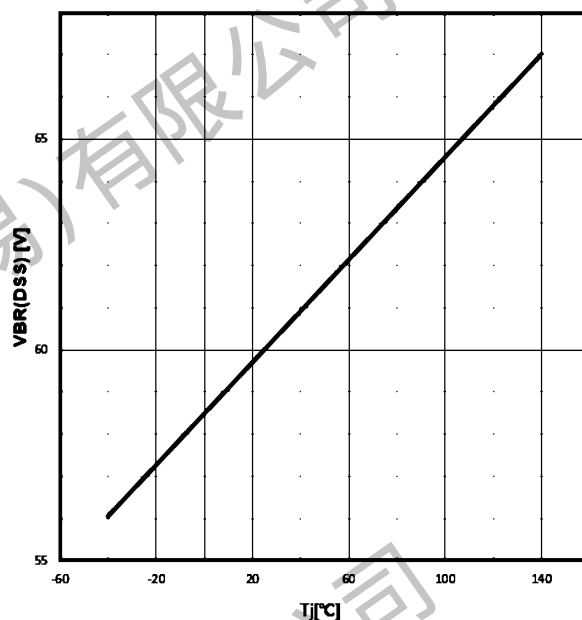
TMG60P06NF

P-Channel Enhancement Mosfet

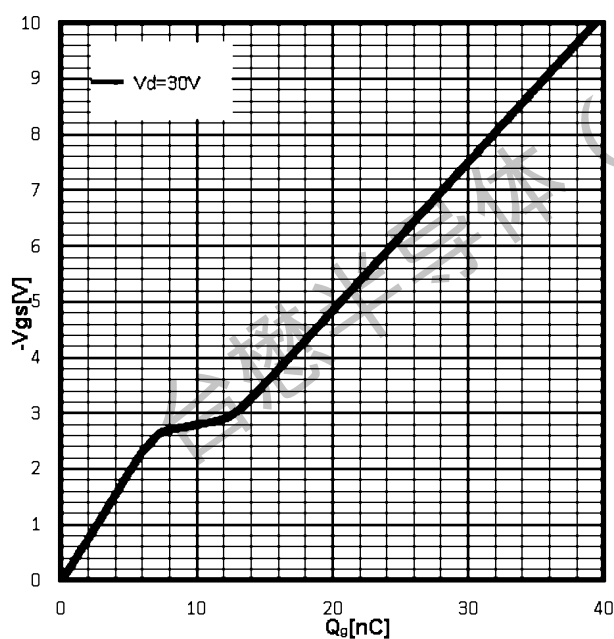
Gate Threshold Voltage
 $-V_{TH}=f(T_j); I_D=-250\mu A$



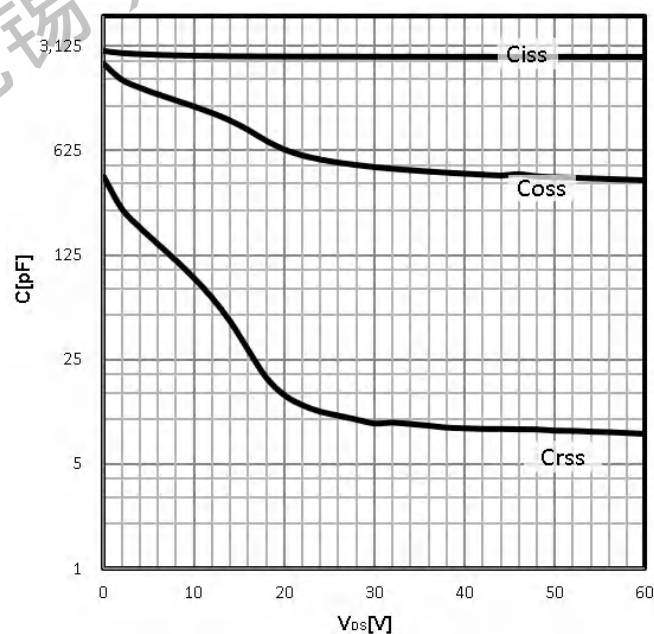
Drain-source breakdown voltage
 $-V_{BR(DSS)}=f(T_j); I_D=-250\mu A$



Typ. gate charge
 $V_{GS}=f(Q_{gate}); I_D=-10A$



Typ. Capacitances
 $C=f(-V_{DS}); V_{GS}=0V; f=1MHz$

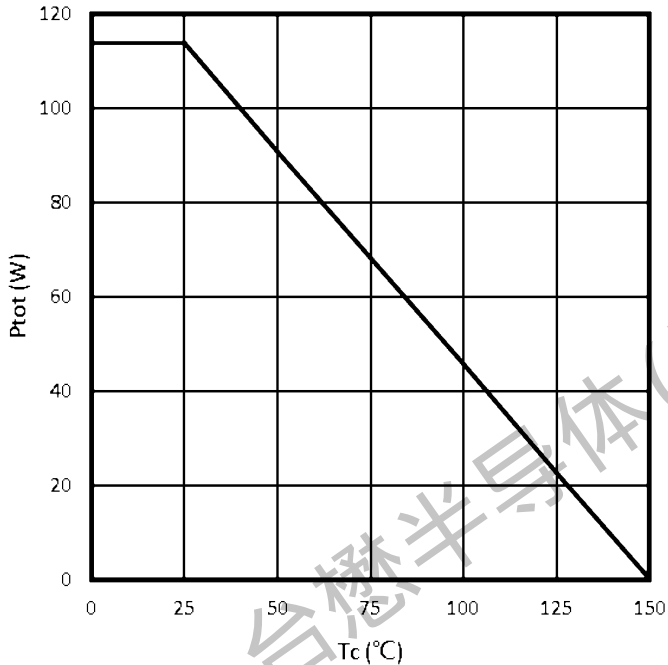


TMG60P06NF

P-Channel Enhancement Mosfet

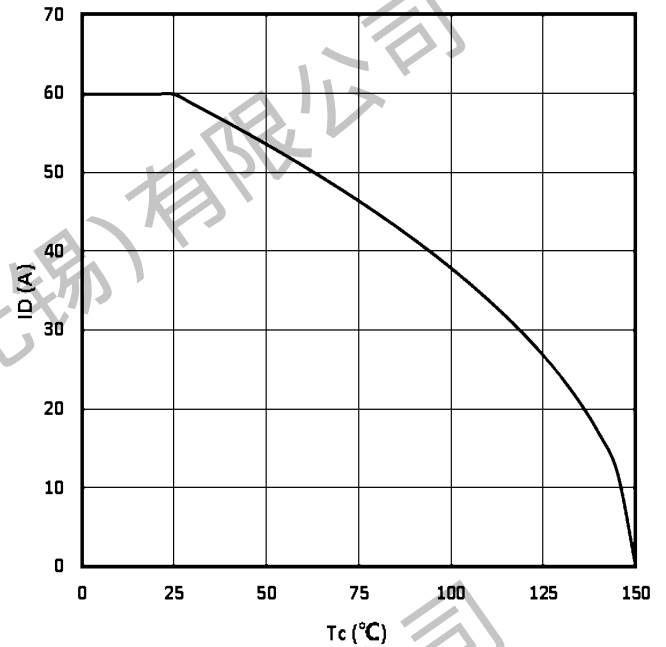
Power Dissipation

$$P_{tot}=f(T_C)$$



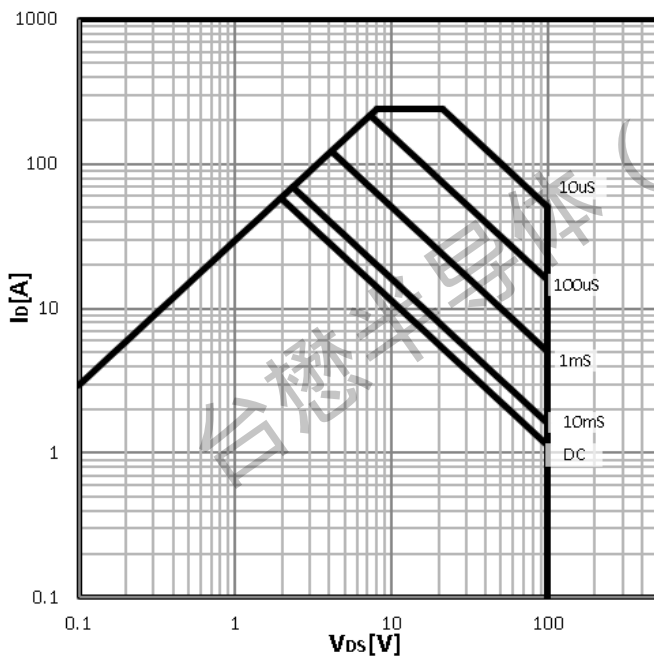
Maximum Drain Current

$$-I_D=f(T_C)$$



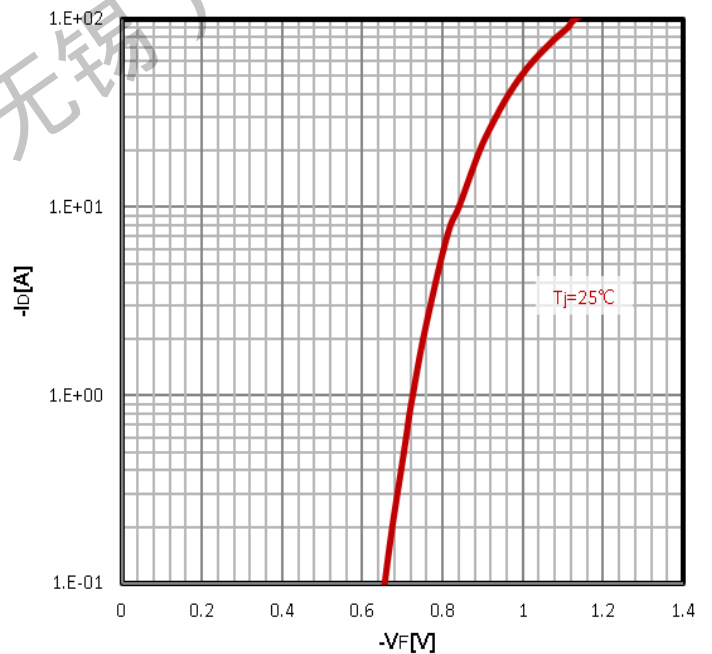
Safe operating area

$$-I_D=f(-V_{DS})$$



Body Diode Forward Voltage Variation

$$-I_F=f(-V_{DS})$$

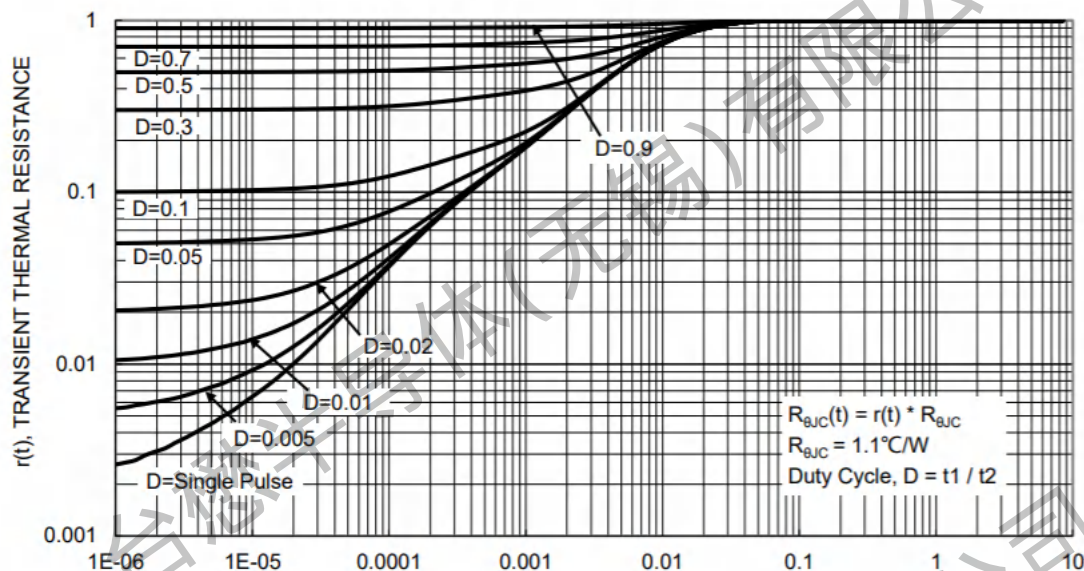


TMG60P06NF

P-Channel Enhancement Mosfet

Max. transient thermal impedance

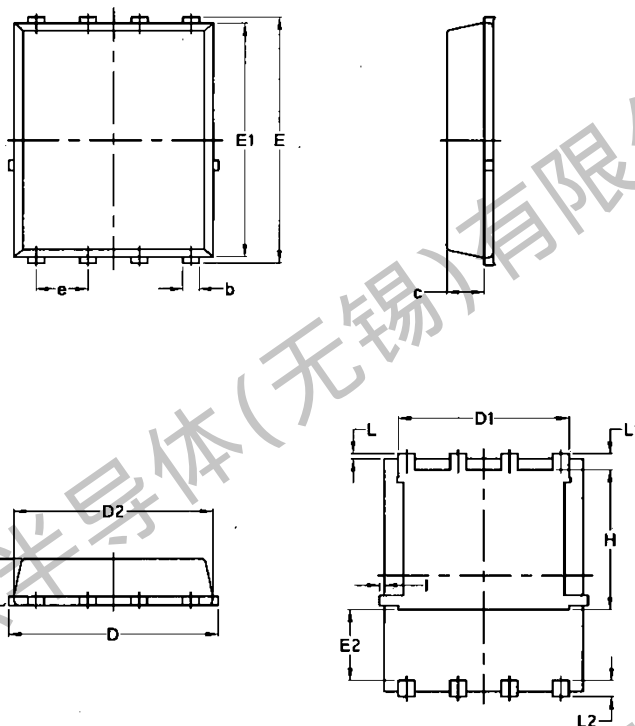
$$Z_{thJC} = f(t_p)$$



TMG60P06NF

P-Channel Enhancement Mosfet

Package Mechanical Data:DFN5x6-8L

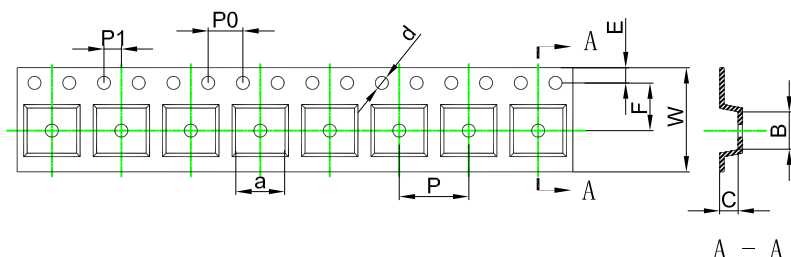


Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

TMG60P06NF

P-Channel Enhancement Mosfet

PDFN5×6-8L Embossed Carrier Tape



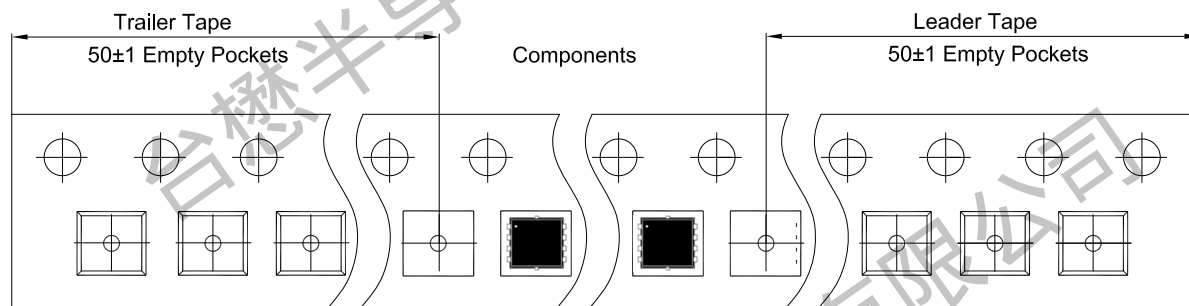
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

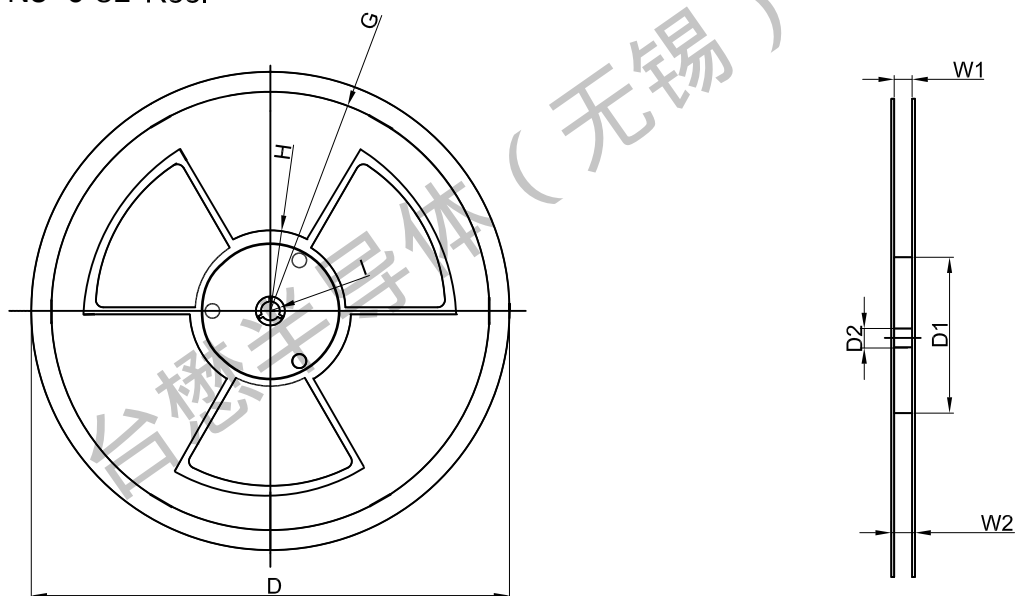
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN5×6-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5×6-8L Tape Leader and Trailer



PDFN5×6-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2023.06.23	23.06	Original	